

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSII)

TPC6101

Notebook PC Applications

Portable Equipment Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 48 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 8.2 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = -10 \text{ }\mu\text{A}$ (max) ($V_{DS} = -20 \text{ V}$)
- Enhancement model: $V_{th} = -0.5 \text{ to } -1.2 \text{ V}$ ($V_{DS} = -10 \text{ V}$, $I_D = -200 \text{ }\mu\text{A}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-20	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	-20	V
Gate-source voltage		V_{GSS}	± 12	V
Drain current	DC (Note 1)	I_D	-4.5	A
	Pulse (Note 1)	I_{DP}	-18	
Drain power dissipation ($t = 5 \text{ s}$) (Note 2a)		P_D	2.2	W
Drain power dissipation ($t = 5 \text{ s}$) (Note 2b)		P_D	0.7	W
Single pulse avalanche energy (Note 3)		E_{AS}	3.3	mJ
Avalanche current		I_{AR}	-2.25	A
Repetitive avalanche energy (Note 4)		E_{AR}	0.22	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

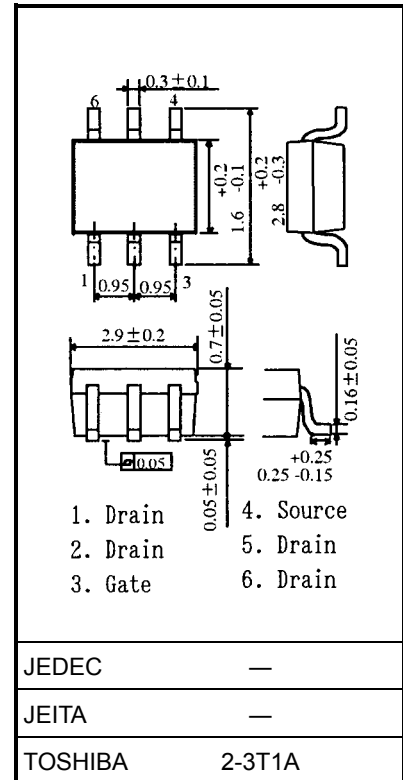
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient ($t = 5 \text{ s}$) (Note 2a)	$R_{th(ch-a)}$	56.8	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ($t = 5 \text{ s}$) (Note 2b)	$R_{th(ch-a)}$	178.5	$^\circ\text{C/W}$

Note: (Note 1), (Note 2), (Note 3), (Note 4), (Note 5) Please see next page.

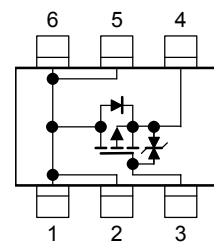
This transistor is an electrostatically sensitive device. Please handle it with caution.

Unit: mm

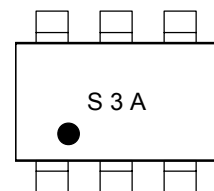


Weight: 0.011 g (typ.)

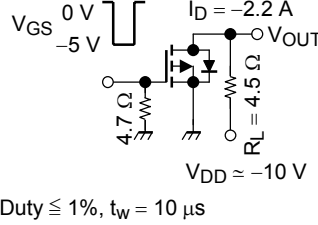
Circuit Configuration



Marking (Note 5)



Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	μA
Drain-source breakdown voltage	$V_{(BR) DSS}$		$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	—	—	V
	$V_{(BR) DSX}$		$I_D = -10 \text{ mA}, V_{GS} = 12 \text{ V}$	-8	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = -10 \text{ V}, I_D = -200 \mu\text{A}$	-0.5	—	-1.2	V
Drain-source ON resistance	$R_{DS(ON)}$		$V_{GS} = -2 \text{ V}, I_D = -2.2 \text{ A}$	—	110	180	m Ω
	$R_{DS(ON)}$		$V_{GS} = -2.5 \text{ V}, I_D = -2.2 \text{ A}$	—	75	100	
	$R_{DS(ON)}$		$V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}$	—	48	60	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -2.2 \text{ A}$	4.1	8.2	—	S
Input capacitance		C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	830	—	pF
Reverse transfer capacitance		C_{rss}		—	300	—	
Output capacitance		C_{oss}		—	370	—	
Switching time	Rise time	t_r		—	6	—	ns
	Turn-ON time	t_{on}		—	11	—	
	Fall time	t_f		—	57	—	
	Turn-OFF time	t_{off}		—	112	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx -16 \text{ V}, V_{GS} = -5 \text{ V}, I_D = -4.5 \text{ A}$	—	12	—	nC
Gate-source charge		Q_{gs}		—	6	—	
Gate-drain ("miller") charge		Q_{gd}		—	6	—	

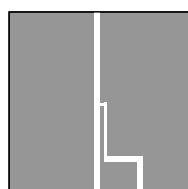
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	-18	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = -4.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V

Note 1: Please use devices on condition that the channel temperature is below 150°C.

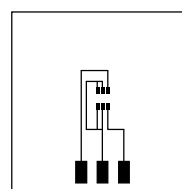
Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)

(b) Device mounted on a glass-epoxy board (b) (t = 5 s)



(a)

FR-4
25.4 × 25.4 × 0.8
Unit: (mm)



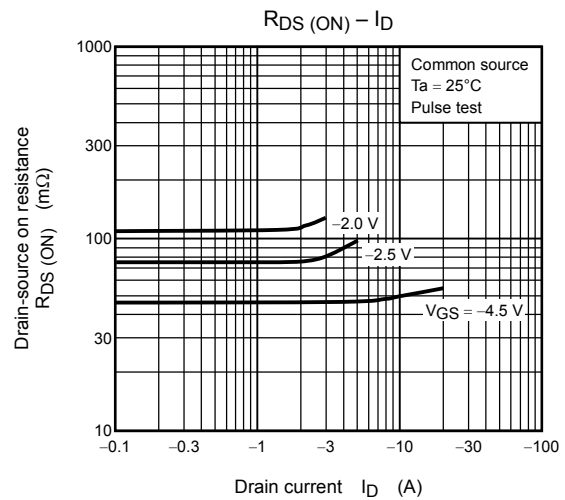
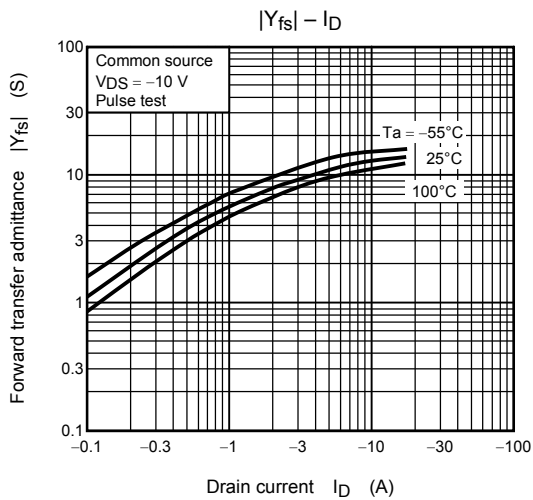
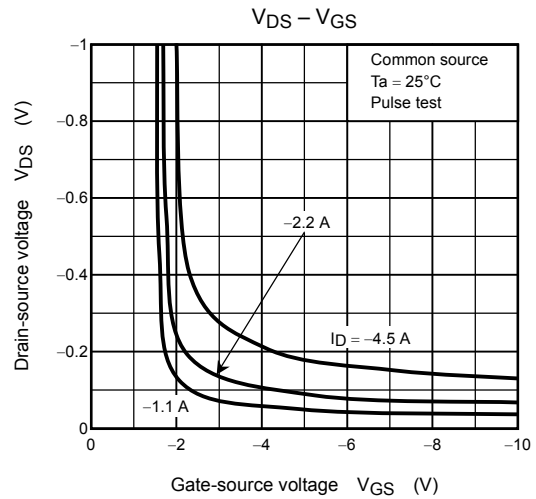
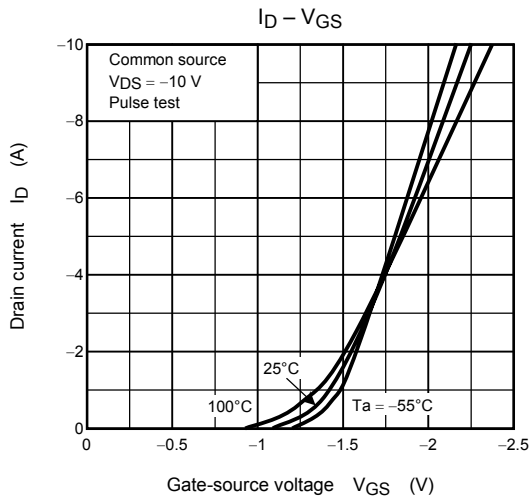
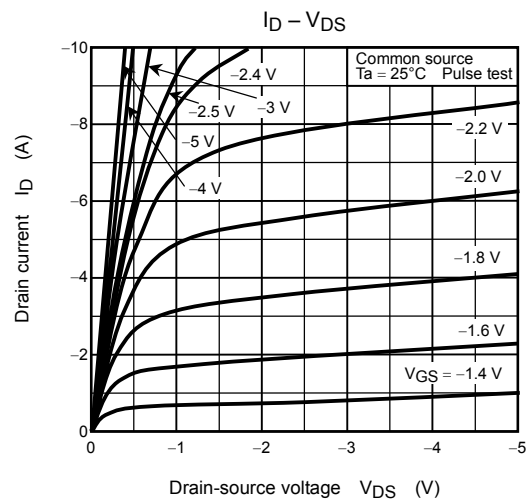
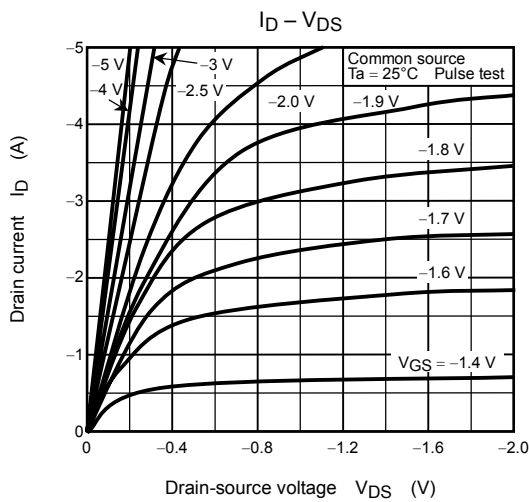
(b)

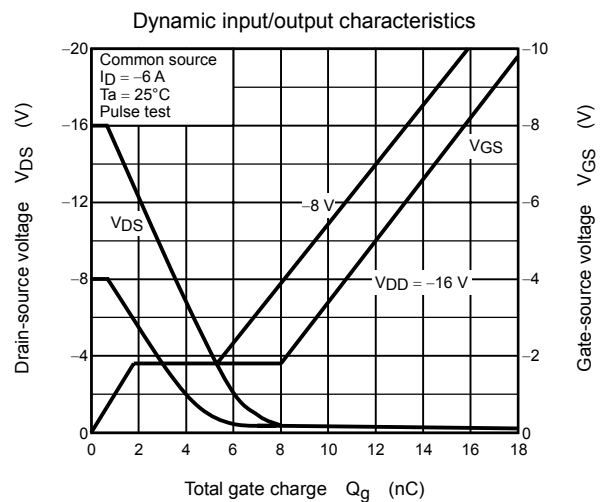
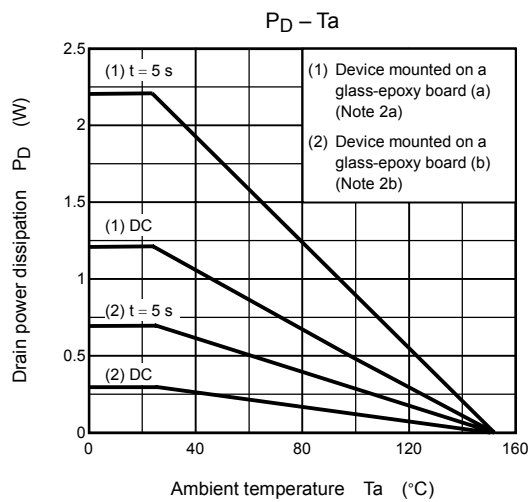
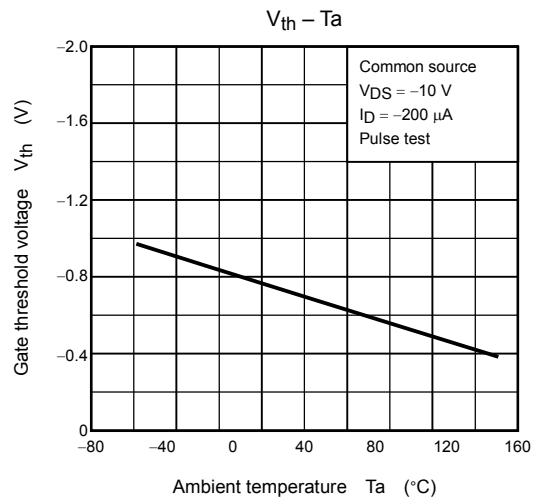
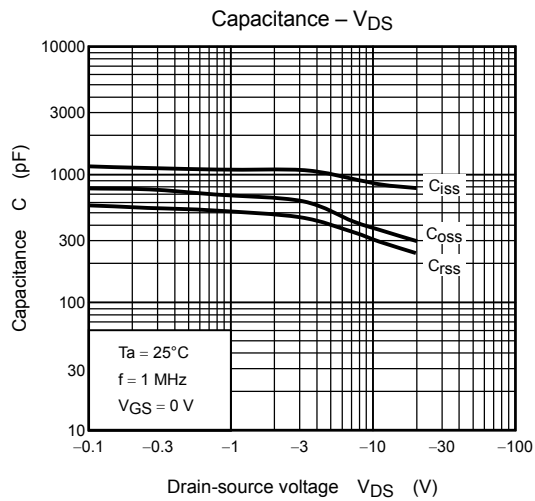
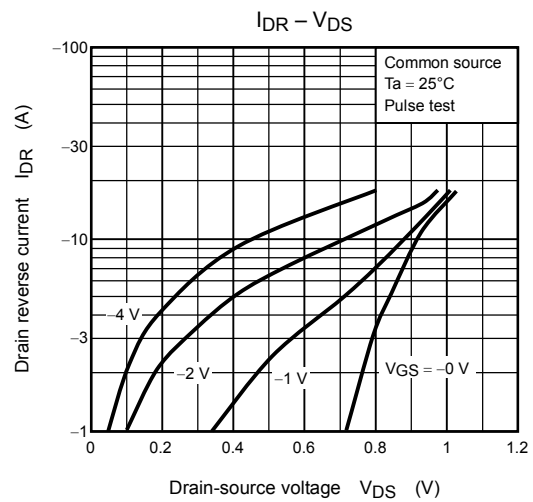
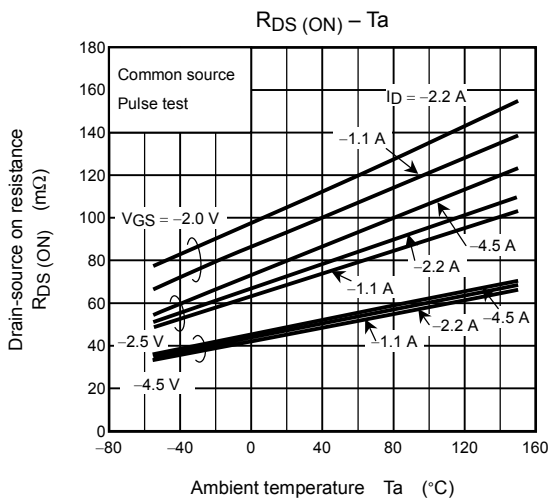
FR-4
25.4 × 25.4 × 0.8
Unit: (mm)

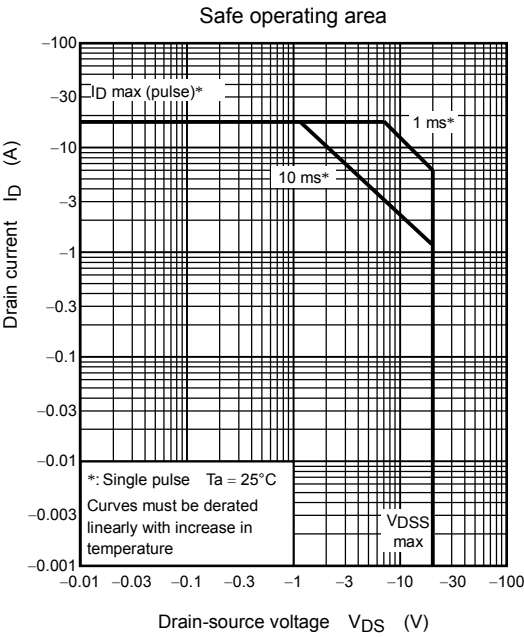
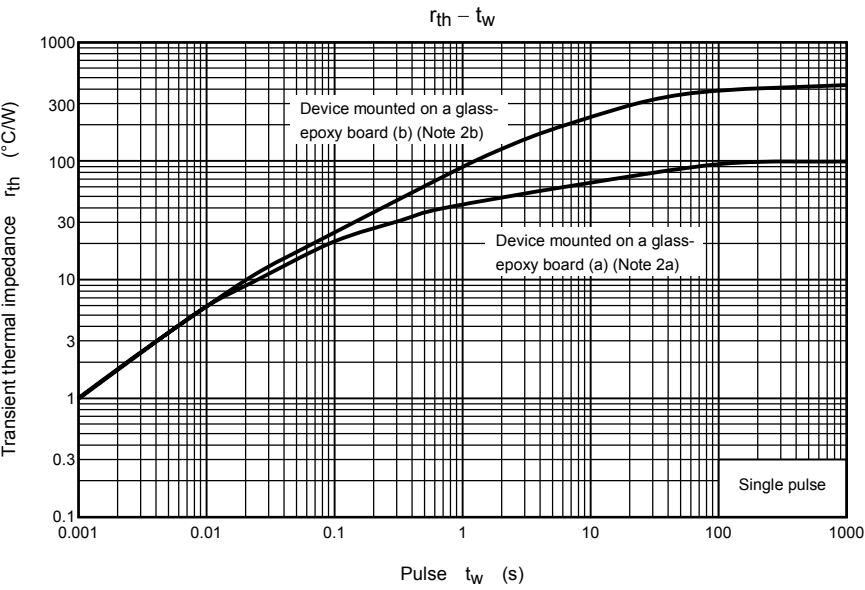
Note 3: $V_{DD} = 16 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 0.5 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = -2.25 \text{ A}$

Note 4: Repetitive rating; pulse width limited by maximum channel temperature

Note 5: Black round marking "•" locates on the left lower side of parts number marking "S3A" indicates terminal No.1.







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